

Dual P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.370 at $V_{GS} = - 4.5$ V	- 1.15
	0.575 at $V_{GS} = - 2.5$ V	- 0.92
	0.800 at $V_{GS} = - 1.8$ V	- 0.78

FEATURES

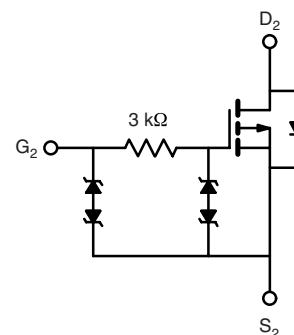
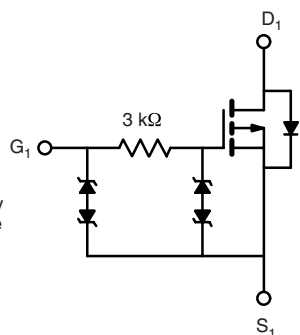
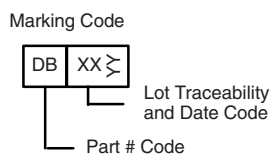
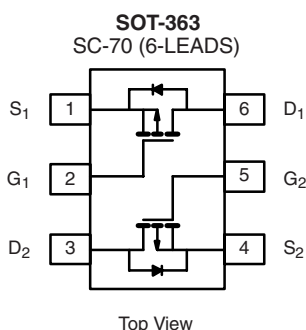
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 1.8 V Rated
- ESD Protected: 3000 V
- Thermally Enhanced SC-70 Package
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switching
- PA Switch
- Level Switch



Ordering Information: Si1917EDH-T1-E3 (Lead (Pb)-free)
Si1917EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 1.15	- 1.00	A
	T _A = 85 °C		- 0.83	- 0.73	
Pulsed Drain Current		I _{DM}	- 3		
Continuous Diode Current (Diode Conduction) ^a		I _S	- 0.61	- 0.47	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	0.73	0.57	W
	T _A = 85 °C		0.38	0.30	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	130	°C/W
	Steady State		170	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	80	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

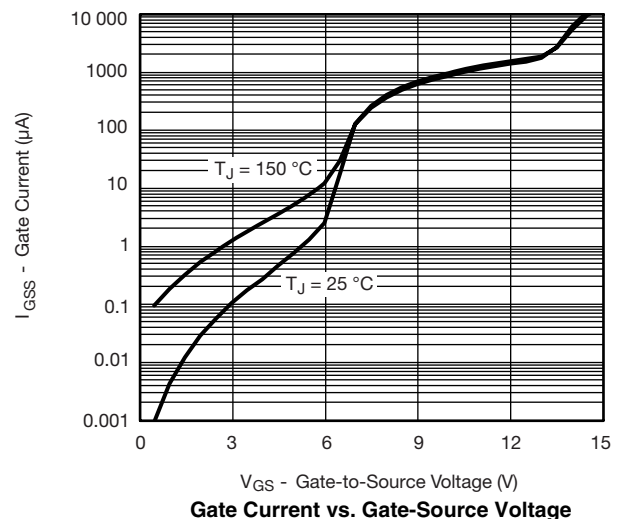
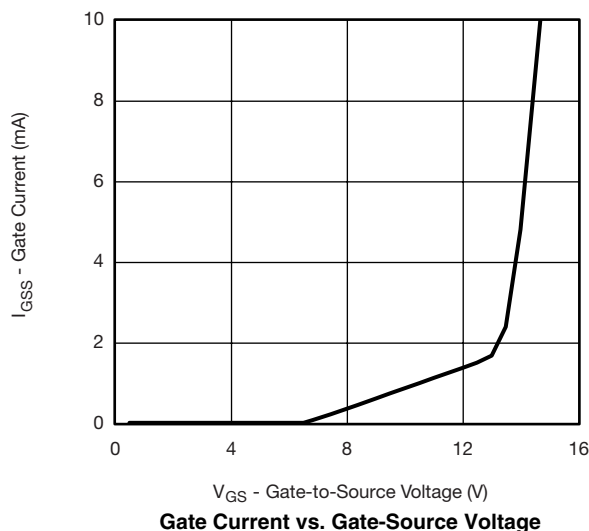
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -100\text{ }\mu\text{A}$	- 0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 4.5\text{ V}$			± 1.5	μA
		$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$			± 10	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$			- 1.0	μA
		$V_{DS} = -9.6\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$			- 5.0	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -4.5\text{ V}$	- 2.0			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -1.0\text{ A}$		0.300	0.370	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -0.81\text{ A}$		0.470	0.575	
		$V_{GS} = -1.8\text{ V}$, $I_D = -0.2\text{ A}$		0.660	0.800	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}$, $I_D = -1.0\text{ A}$		1.7		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.47\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.85	- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -1.0\text{ A}$		1.3	2.0	nC
Gate-Source Charge	Q_{gs}			0.31		
Gate-Drain Charge	Q_{gd}			0.31		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}$, $R_L = 12\text{ }\Omega$ $I_D \cong -0.5\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 6\text{ }\Omega$		0.17	0.26	μs
Rise Time	t_r			0.47	0.71	
Turn-Off Delay Time	$t_{d(off)}$			0.96	1.4	
Fall Time	t_f			1.0	1.5	

Notes

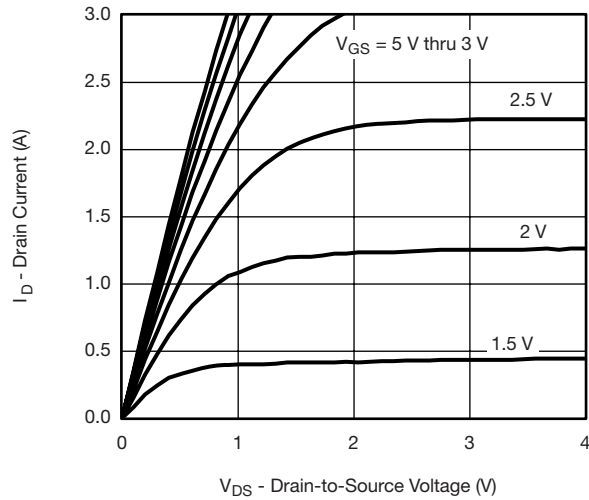
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

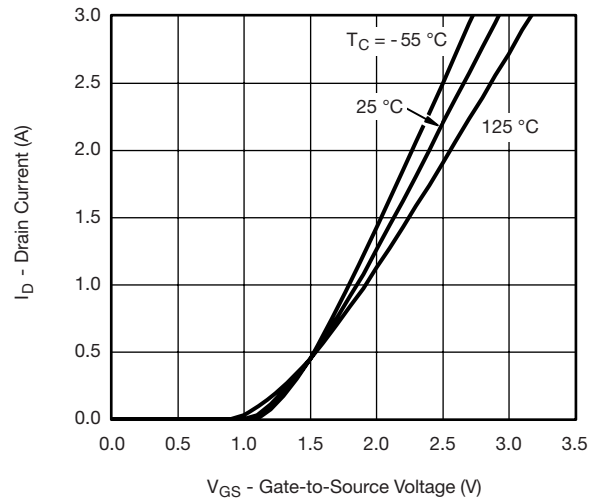
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

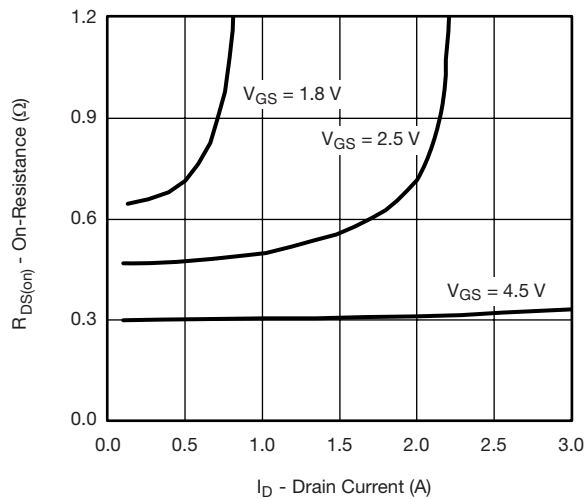
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



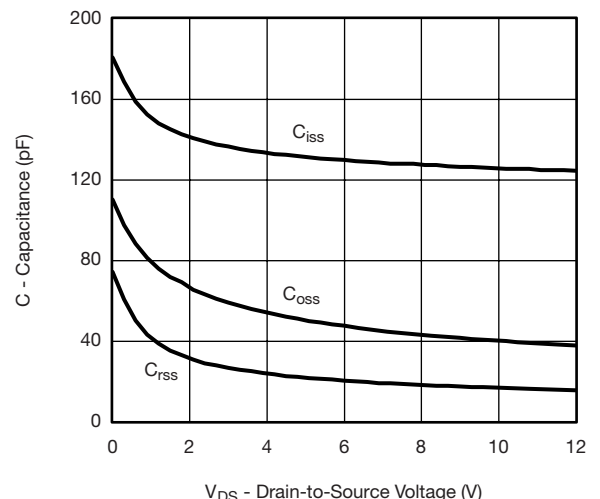
Output Characteristics



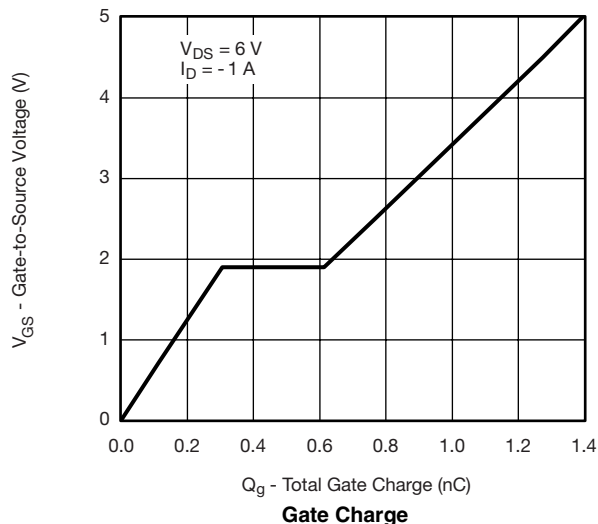
Transfer Characteristics



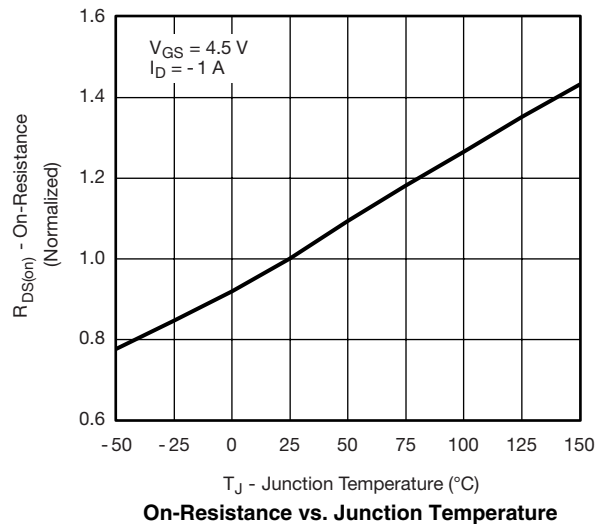
On-Resistance vs. Drain Current



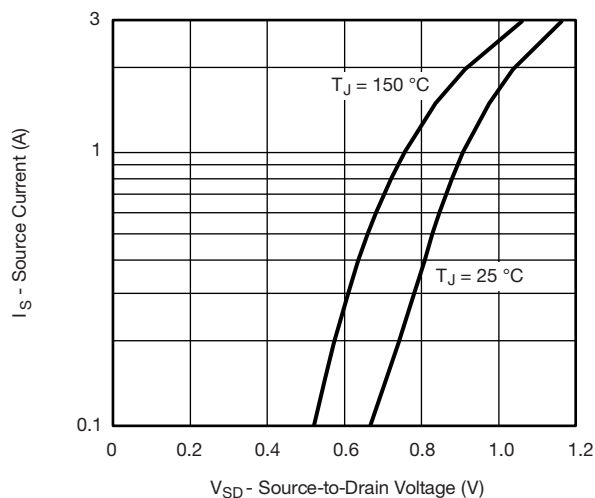
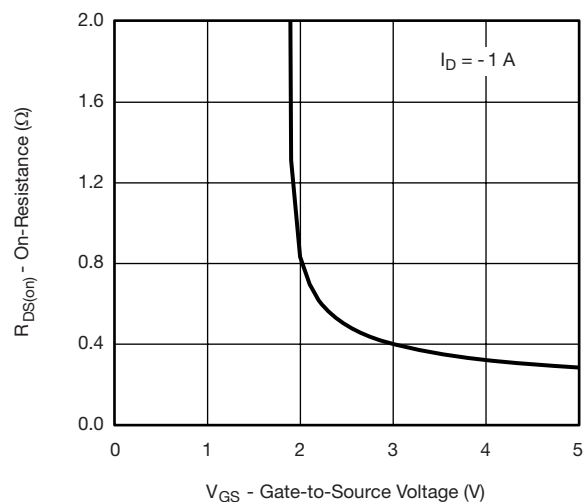
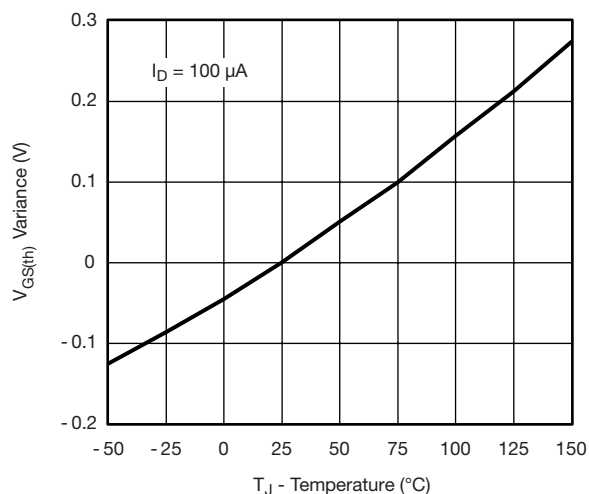
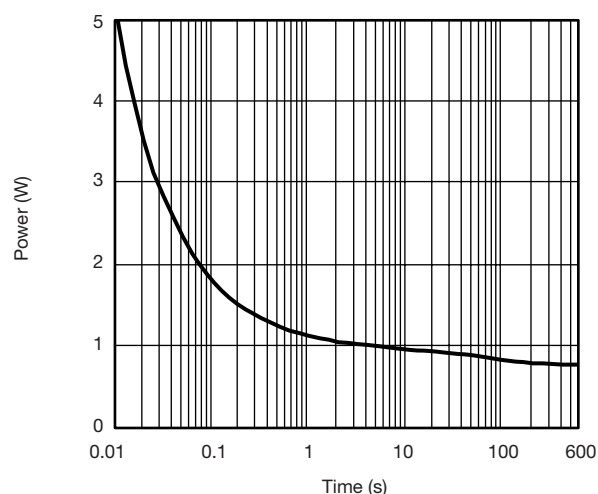
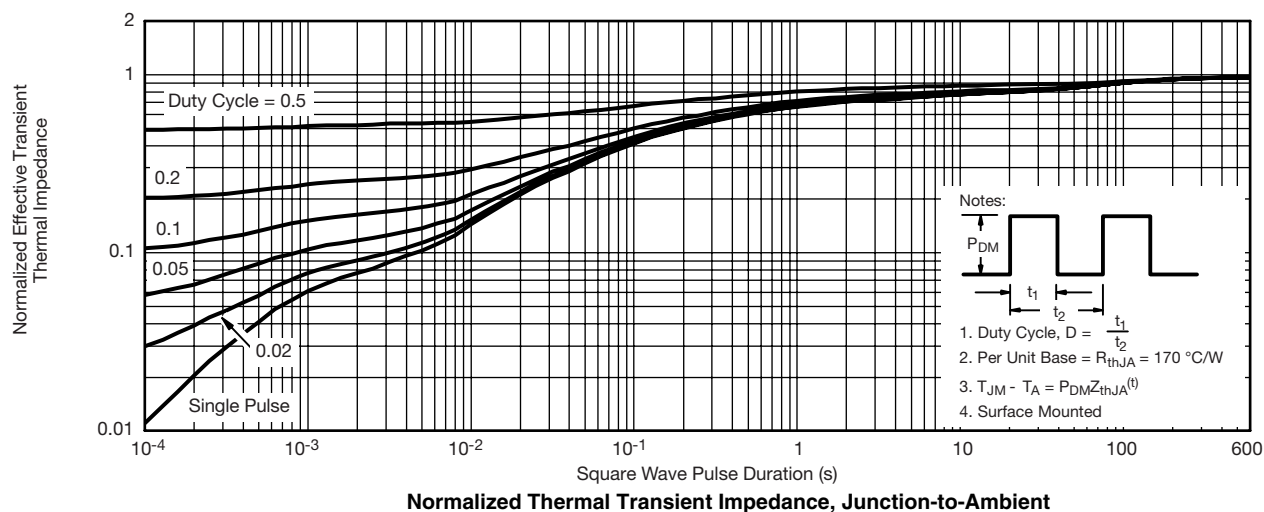
Capacitance



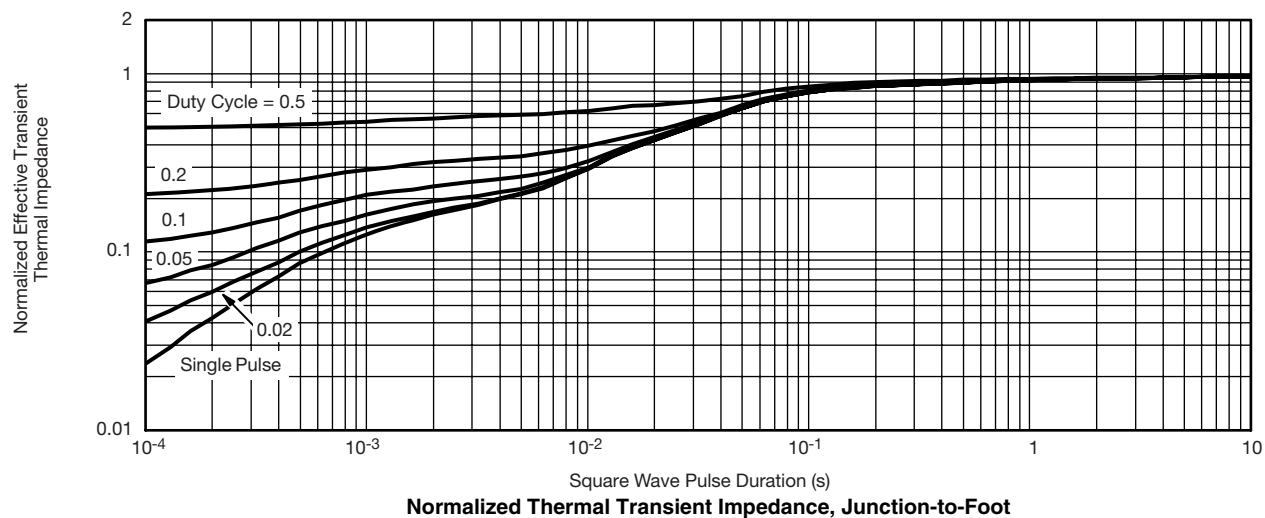
Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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